



STS2300S

SamHop Microelectronics Corp.

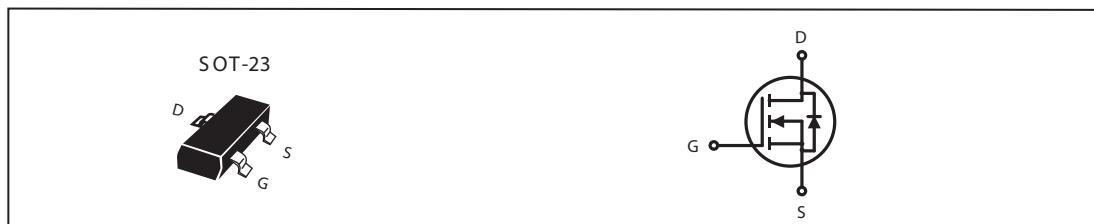
Sep. 8 2005

N-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
V _{DSS}	I _D	R _{DSON} (mΩ) Max
20V	6A	35 @ V _{GS} = 4.5V 45 @ V _{GS} = 2.5V

FEATURES

- Super high dense cell design for low R_{DSON}.
- Rugged and reliable.
- SOT-23 package.



ABSOLUTE MAXIMUM RATING (T_A=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	20	V
Gate-Source Voltage	V _{GS}	±12	V
Drain Current-Continuous @ T _J =25°C -Pulsed ^b	I _D	6	A
	I _{DM}	20	A
Drain-Source Diode Forward Current	I _S	1.25	A
Maximum Power Dissipation ^a	P _D	1.25	W
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient ^a	R _{thJA}	100	°C/W
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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}} = 0\text{V}, I_{\text{D}} = 250\mu\text{A}$	20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}} = 16\text{V}, V_{\text{GS}} = 0\text{V}$		1		μA
Gate-Body Leakage	I_{GSS}	$V_{\text{GS}} = \pm 10\text{V}, V_{\text{DS}} = 0\text{V}$		± 100		nA
ON CHARACTERISTICS^b						
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_{\text{D}} = 250\mu\text{A}$	0.5	0.8	1.3	V
Drain-Source On-State Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}} = 4.5\text{V}, I_{\text{D}} = 4\text{A}$		30	35	m-ohm
		$V_{\text{GS}} = 2.5\text{V}, I_{\text{D}} = 2\text{A}$		38	45	m-ohm
On-State Drain Current	$I_{\text{D}(\text{ON})}$	$V_{\text{DS}} = 5\text{V}, V_{\text{GS}} = 4.5\text{V}$	6			A
Forward Transconductance	g_{FS}	$V_{\text{DS}} = 5\text{V}, I_{\text{D}} = 4\text{A}$		18.1		S
DYNAMIC CHARACTERISTICS^c						
Input Capacitance	C_{ISS}	$V_{\text{DS}} = 15\text{V}, V_{\text{GS}} = 0\text{V}$ $f = 1.0\text{MHz}$		803		pF
Output Capacitance	C_{OSS}			120		pF
Reverse Transfer Capacitance	C_{RSS}			85		pF
SWITCHING CHARACTERISTICS^c						
Turn-On Delay Time	$t_{\text{D}(\text{ON})}$	$V_{\text{DD}} = 10\text{V},$ $I_{\text{D}} = 1\text{A},$ $V_{\text{GS}} = 4.5\text{V},$ $R_{\text{GEN}} = 6 \text{ ohm}$		15		ns
Rise Time	t_{r}			18		ns
Turn-Off Delay Time	$t_{\text{D}(\text{OFF})}$			78		ns
Fall Time	t_{f}			27		ns
Total Gate Charge	Q_g	$V_{\text{DS}} = 10\text{V}, I_{\text{D}} = 4\text{A},$ $V_{\text{GS}} = 4.5\text{V}$		8.8		nC
Gate-Source Charge	Q_{gs}			1.8		nC
Gate-Drain Charge	Q_{gd}			3.9		nC

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ELECTRICAL CHARACTERISTICS ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS ^b						
Diode Forward Voltage	V_{SD}	$V_{GS} = 0V, I_S = 1.25A$		0.8	1.2	V

Notes

- a. Surface Mounted on FR4 Board, $t \leq 10\text{ sec}$.
- b. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
- c. Guaranteed by design, not subject to production testing.

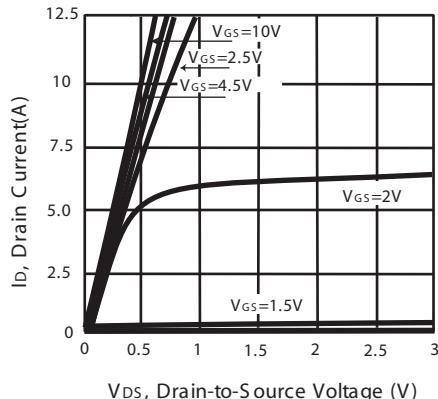


Figure 1. Output Characteristics

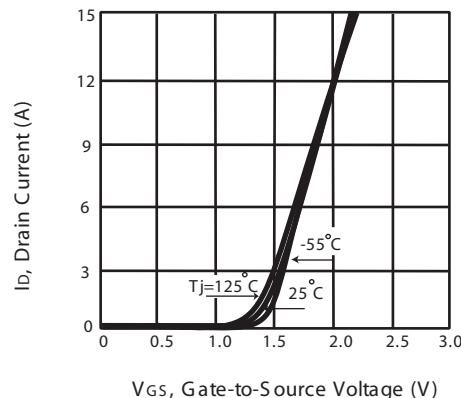


Figure 2. Transfer Characteristics

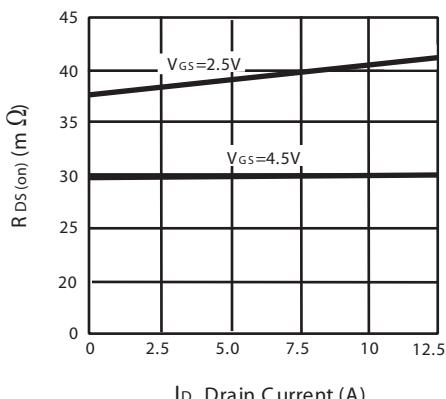


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

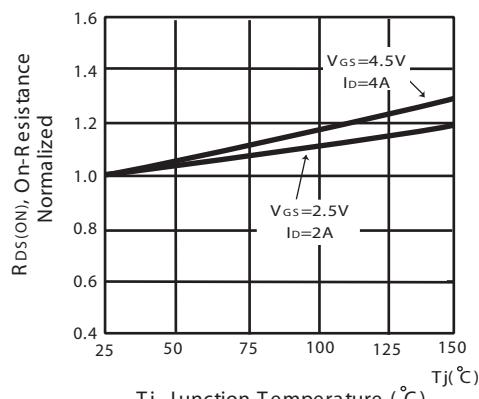


Figure 4. On-Resistance Variation with Drain Current and Temperature

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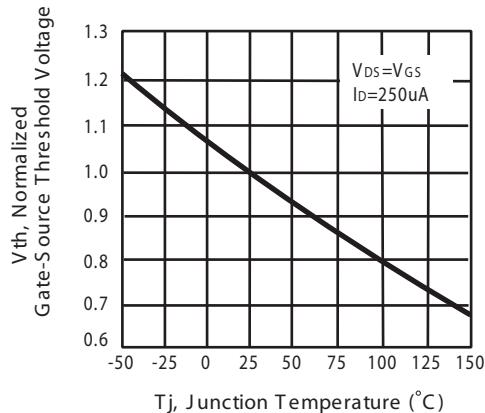


Figure 5. Gate Threshold Variation with Temperature

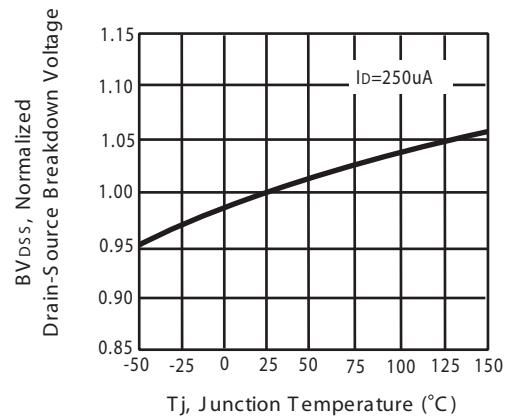


Figure 6. Breakdown Voltage Variation with Temperature

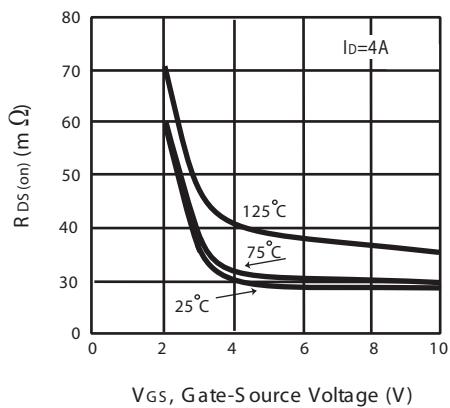


Figure 7. On-Resistance vs. Gate-Source Voltage

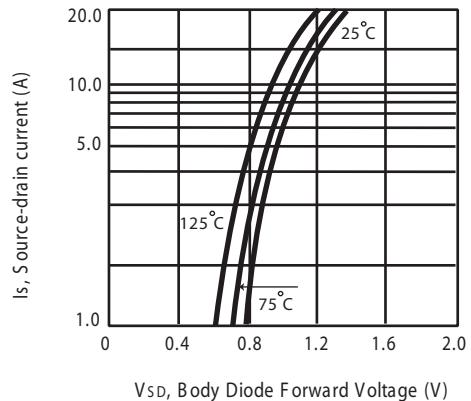


Figure 8. Body Diode Forward Voltage Variation with Source Current

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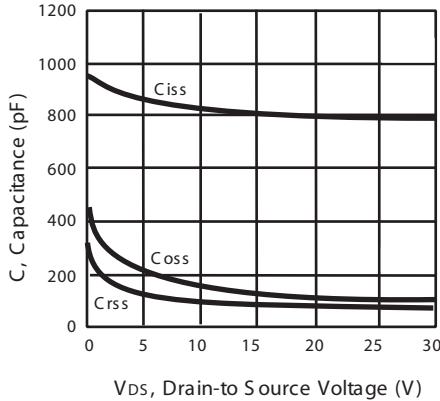


Figure 9. Capacitance

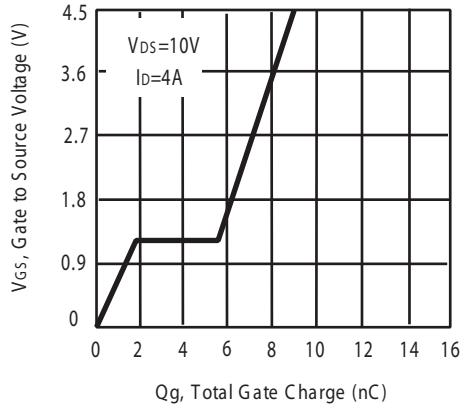


Figure 10. Gate Charge

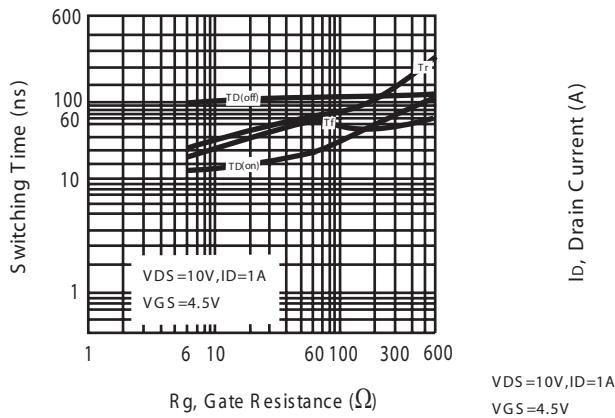


Figure 11. switching characteristics

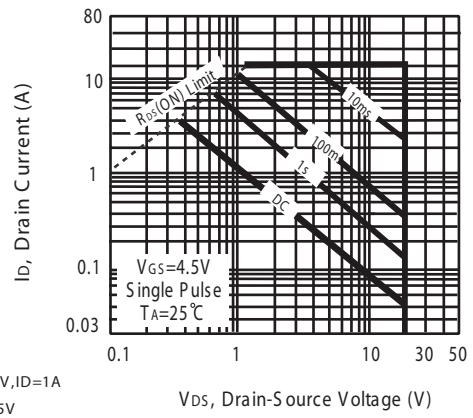


Figure 12. Maximum Safe Operating Area

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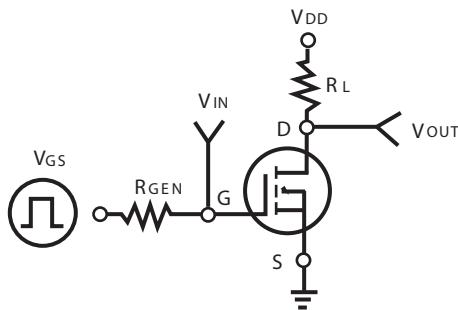


Figure 11. Switching Test Circuit

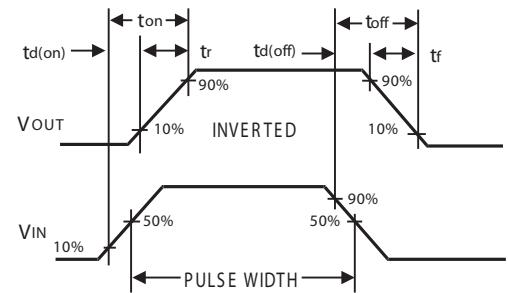
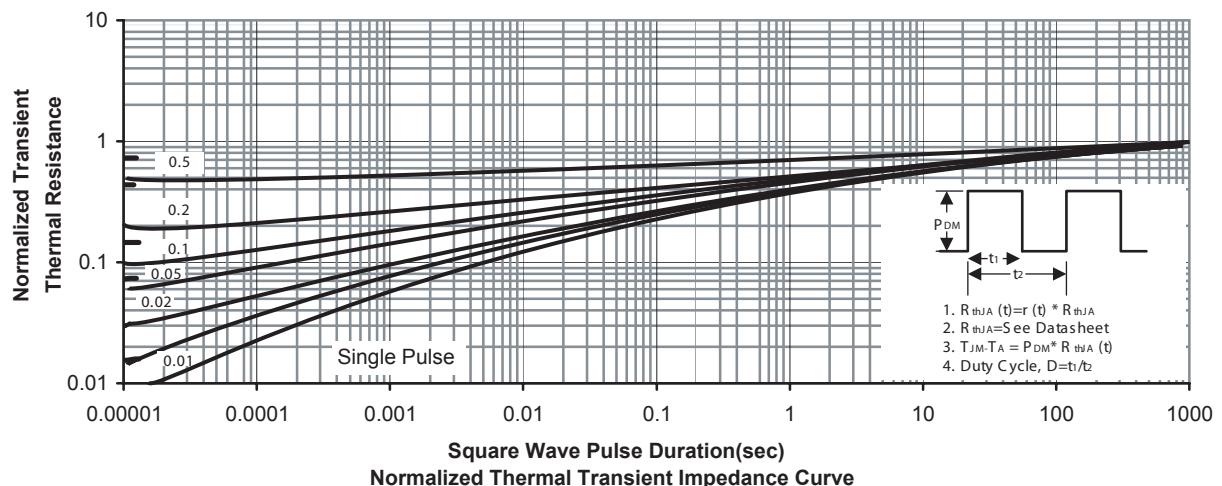


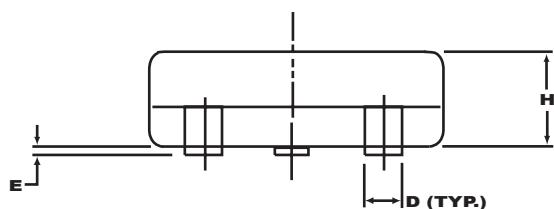
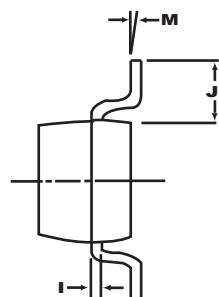
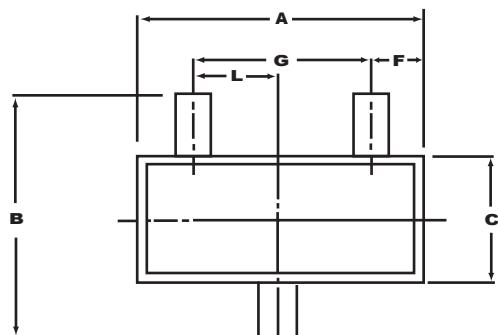
Figure 12. Switching Waveforms



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PACKAGE OUTLINE DIMENSIONS

SOT-23

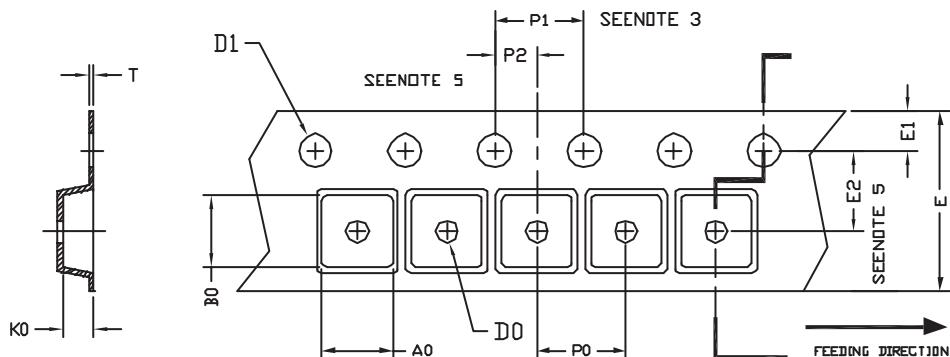


SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.70	3.10	0.106	0.122
B	2.40	2.80	0.094	0.110
C	1.40	1.60	0.055	0.063
D	0.35	0.50	0.014	0.020
E	0	0.10	0	0.004
F	0.45	0.55	0.018	0.022
G	1.90 REF.		0.075 REF.	
H	1.00	1.30	0.039	0.051
I	0.10	0.20	0.004	0.008
J	0.40	-	0.016	-
L	0.45	1.15	0.033	0.045
M	0°	10°	0°	10°

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SOT-23 Tape and Reel Data

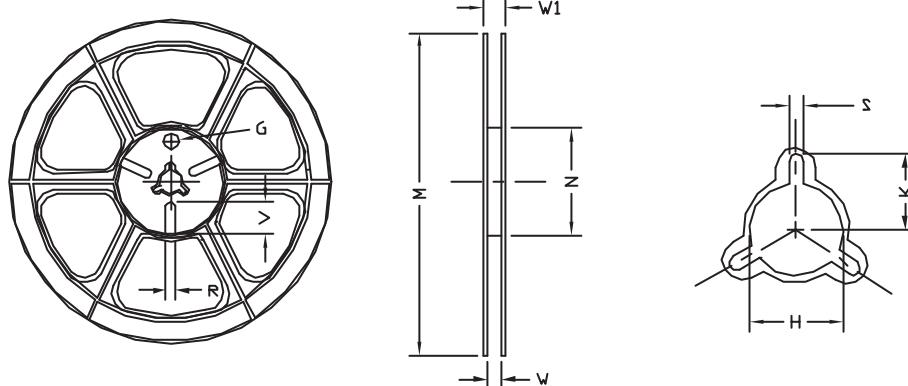
SOT-23 Carrier Tape



UNIT:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SOT-23	3.20 ±0.10	3.00 ±0.10	1.33 ±0.10	§ 1.00 +0.25	§ 1.50 +0.10	8.00 +0.30 -0.10	1.75 ±0.10	3.50 ±0.05	4.00 ±0.10	4.00 ±0.10	2.00 ±0.05	0.20 ±0.02

SOT-23 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
8mm	§ 178	§ 178 ±1	§ 60 ±1	9.00 ±0.5	12.00 ±0.5	§ 13.5 ±0.5	10.5	2.00 ±0.5	§ 10.0	5.00	18.00